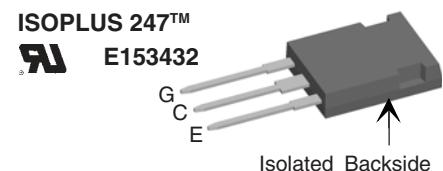
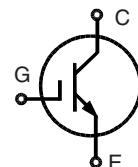


## NPT<sup>3</sup> IGBT

in ISOPLUS 247™

**I<sub>C25</sub>** = 95 A  
**V<sub>CES</sub>** = 1200 V  
**V<sub>CE(sat) typ.</sub>** = 2.1 V



G = Gate      C = Collector      E = Emitter

### IGBT

Symbol	Conditions	Maximum Ratings		
V <sub>CES</sub>	T <sub>VJ</sub> = 25°C to 150°C	1200	V	
V <sub>GES</sub>		± 20	V	
I <sub>C25</sub>	T <sub>C</sub> = 25°C	95	A	
I <sub>C90</sub>	T <sub>C</sub> = 90°C	60	A	
I <sub>CM</sub>	V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 22 Ω; T <sub>VJ</sub> = 125°C RBSOA, Clamped inductive load; L = 100 μH	100	A	
V <sub>CEK</sub>		V <sub>CES</sub>		
t <sub>sc</sub> (SCSOA)	V <sub>CE</sub> = 900 V; V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 22 Ω; T <sub>VJ</sub> = 125°C non-repetitive	10	μs	
P <sub>tot</sub>	T <sub>C</sub> = 25°C	375	W	

Symbol	Conditions	Characteristic Values		
		(T <sub>VJ</sub> = 25°C, unless otherwise specified)	min.	typ.
V <sub>CE(sat)</sub>	I <sub>C</sub> = 60 A; V <sub>GE</sub> = 15 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C	2.1 2.5	2.7	V
V <sub>GE(th)</sub>	I <sub>C</sub> = 2 mA; V <sub>GE</sub> = V <sub>CE</sub>	4.5	6.5	V
I <sub>CES</sub>	V <sub>CE</sub> = V <sub>CES</sub> ; V <sub>GE</sub> = 0 V; T <sub>VJ</sub> = 25°C T <sub>VJ</sub> = 125°C	0.1	0.1	mA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V; V <sub>GE</sub> = ± 20 V		200	nA
t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub>	Inductive load, T <sub>VJ</sub> = 125°C V <sub>CE</sub> = 600 V; I <sub>C</sub> = 60 A V <sub>GE</sub> = ±15 V; R <sub>G</sub> = 22 Ω	80 50 680 30 7.2 4.8	ns ns ns ns mJ mJ	
C <sub>ies</sub>		3.8	nF	
Q <sub>Gon</sub>		350	nC	
R <sub>thJC</sub>			0.33	K/W
R <sub>thJH</sub>		0.66		K/W

### Features

- NPT<sup>3</sup> IGBT
  - low saturation voltage
  - positive temperature coefficient for easy paralleling
  - fast switching
  - short tail current for optimized performance in resonant circuits
- ISOPLUS 247™ package
  - isolated back surface
  - low coupling capacity between pins and heatsink
  - high reliability
  - industry standard outline

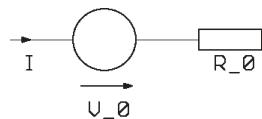
### Applications

- single switches and with complementary free wheeling diodes
- choppers
- phaselegs, H bridges, three phase bridges e.g. for
  - power supplies, UPS
  - AC, DC and SR drives
  - induction heating

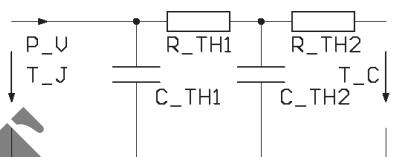
**Component**

Symbol	Conditions	Maximum Ratings		
$T_{VJ}$		-55...+150	°C	
$T_{stg}$		-55...+125	°C	
$V_{ISOL}$	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$	2500	V~	
$F_c$	mounting force with clip	20...120	N	

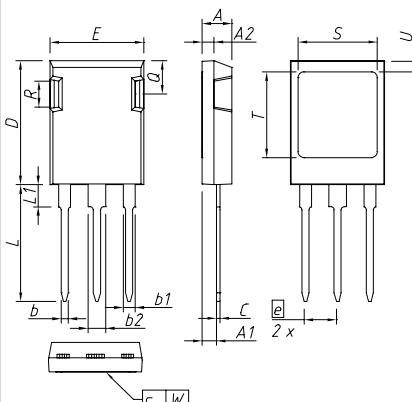
Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$C_p$	coupling capacity between shorted pins and mounting tab in the case	30	pF	
<b>Weight</b>		6	g	

**Equivalent Circuits for Simulation****Conduction**

IGBT (typ. at  $V_{GE} = 15 \text{ V}$ ;  $T_J = 125^\circ\text{C}$ )  
 $V_0 = 0.99 \text{ V}$ ;  $R_0 = 25 \text{ m}\Omega$

**Thermal Response**

IGBT (typ.)  
 $C_{th1} = 0.13 \text{ J/K}$ ;  $R_{th1} = 0.06 \text{ K/W}$   
 $C_{th2} = 0.32 \text{ J/K}$ ;  $R_{th2} = 0.27 \text{ K/W}$

**ISOPLUS247™ OUTLINE**

DIM.	MILLIMETER		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,29	2,54	0,090	0,100
A2	1,91	2,16	0,075	0,085
b	1,14	1,40	0,045	0,055
b1	1,91	2,15	0,075	0,085
b2	2,92	3,20	0,115	0,126
C	0,61	0,83	0,024	0,033
D	20,80	21,34	0,819	0,840
E	15,75	16,13	0,620	0,635
e	5,45 BSC		0,215 BSC	
L	19,81	20,60	0,780	0,811
L1	3,81	4,38	0,150	0,172
Q	5,59	6,20	0,220	0,244
R	4,32	4,85	0,170	0,191
S	13,21	13,72	0,520	0,540
T	15,75	16,26	0,620	0,640
U	1,65	2,03	0,065	0,080
W	-	0,10	-	0,004

The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side  
This drawing will meet all dimensions requirement of JEDEC outline TO-247 AD except screw hole and except Lmax.

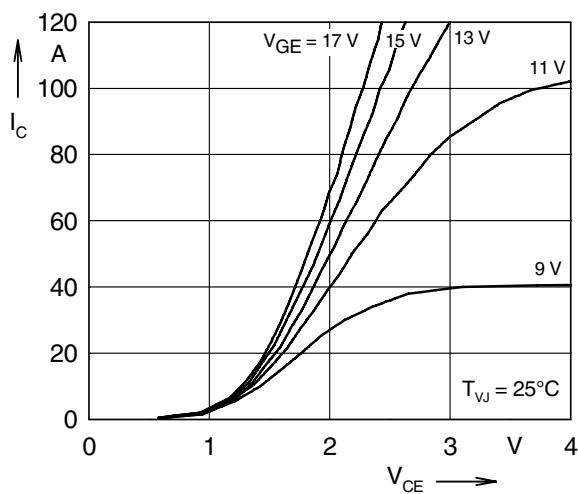


Fig. 1 Typ. output characteristics

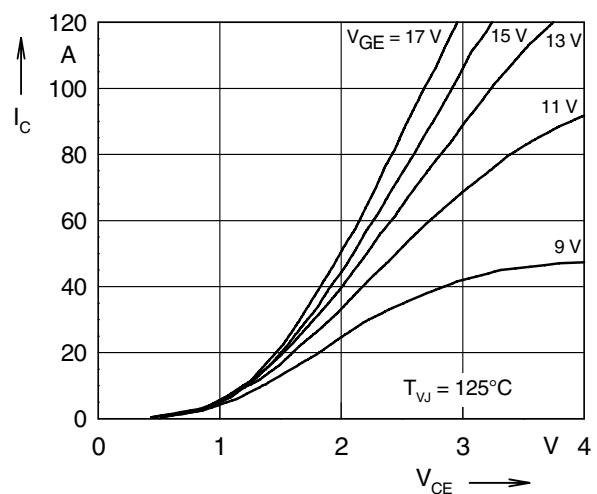


Fig. 2 Typ. output characteristics

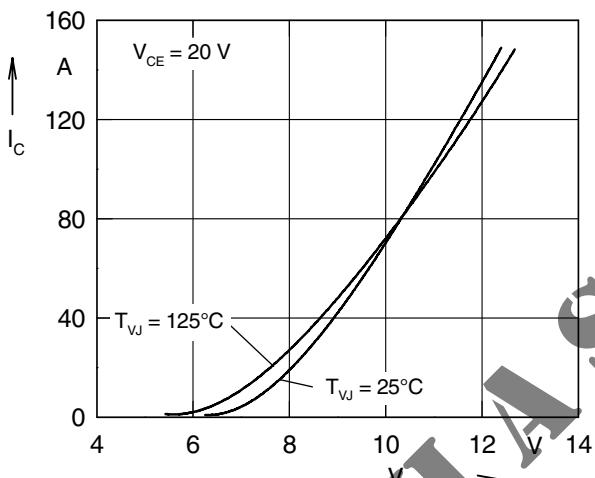


Fig. 3 Typ. transfer characteristics

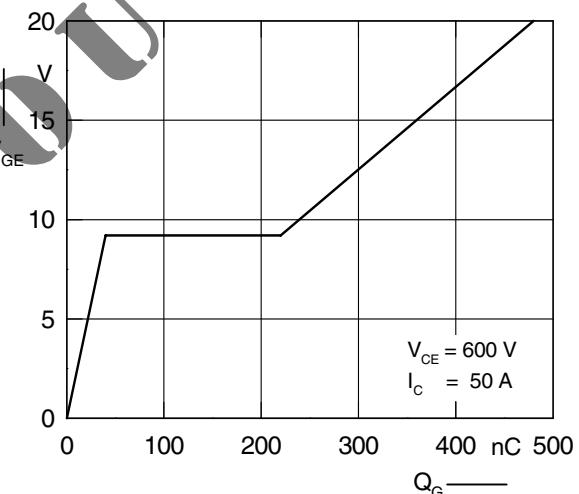


Fig. 4 Typ. turn on gate charge

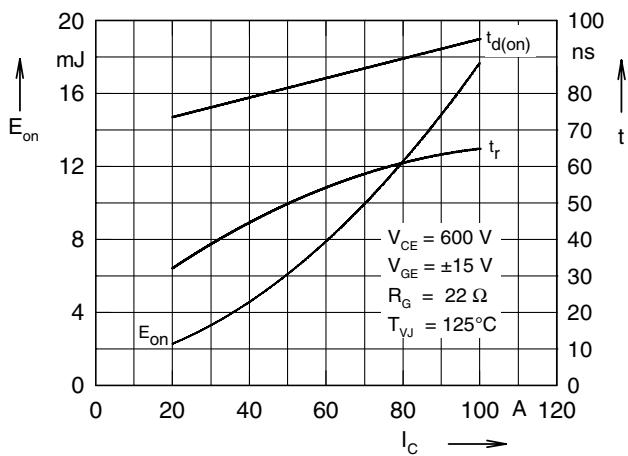


Fig. 5 Typ. turn on energy and switching times versus collector current

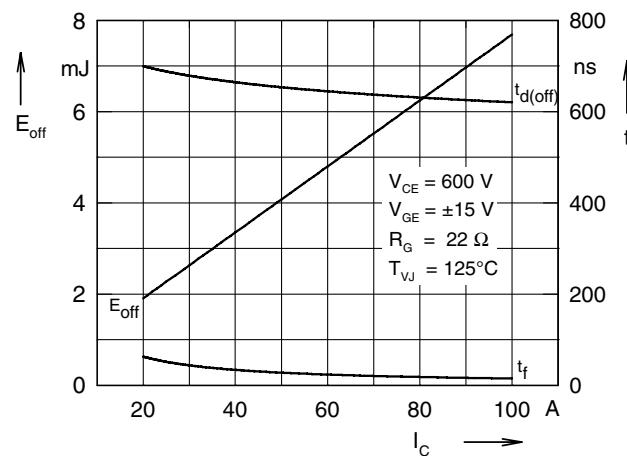


Fig. 6 Typ. turn off energy and switching times versus collector current

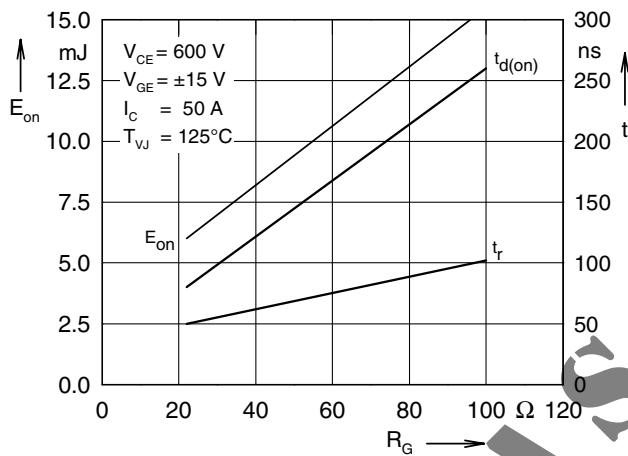


Fig. 7 Typ. turn on energy and switching times versus gate resistor

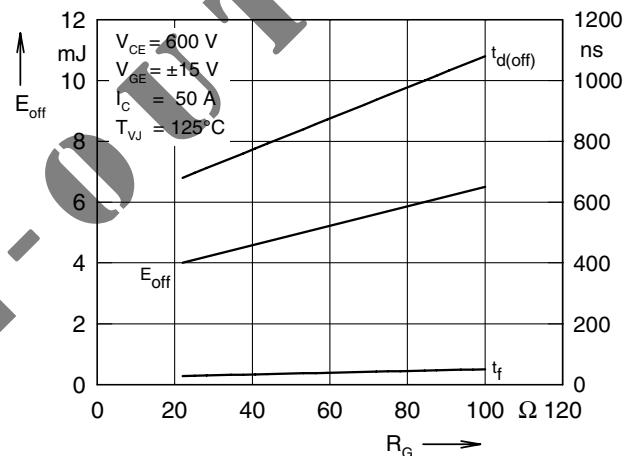


Fig. 8 Typ. turn off energy and switching times versus gate resistor

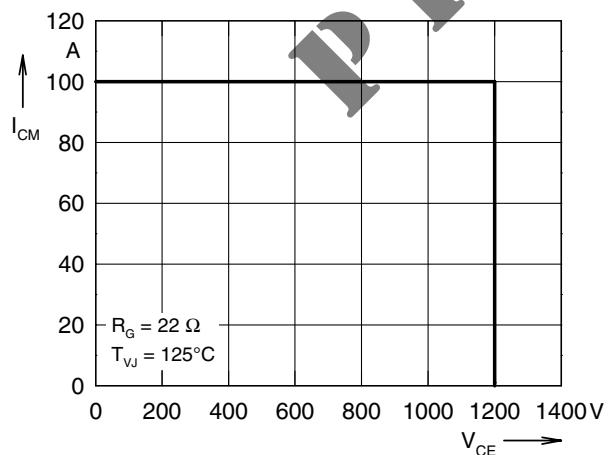


Fig. 9 Reverse biased safe operating area RBSOA

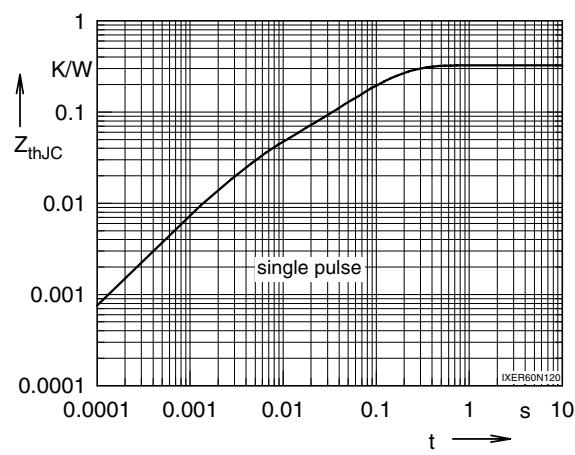


Fig. 10 Typ. transient thermal impedance